

Min Liao

List of Publications by Year in descending order

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33
papers

1,270
citations

361413

20
h-index

395702

33
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33
all docs

33
docs citations

33
times ranked

1998
citing authors

#	ARTICLE	IF	CITATIONS
1	Lithiophilic montmorillonite serves as lithium ion reservoir to facilitate uniform lithium deposition. Nature Communications, 2019, 10, 4973.	12.8	144
2	Modulating the d-band center of boron doped single-atom sites to boost the oxygen reduction reaction. Journal of Materials Chemistry A, 2019, 7, 20952-20957.	10.3	117
3	2D Nanomaterial Arrays for Electronics and Optoelectronics. Advanced Functional Materials, 2018, 28, 1706559.	14.9	101
4	A Novel Conductive Mesoporous Layer with a Dynamic Two-Step Deposition Strategy Boosts Efficiency of Perovskite Solar Cells to 20%. Advanced Materials, 2018, 30, e1801935.	21.0	99
5	Performance Improvement of Hf _{0.5} Zr _{0.5} O ₂ -Based Ferroelectric-Field-Effect Transistors With ZrO ₂ Seed Layers. IEEE Electron Device Letters, 2019, 40, 714-717.	3.9	95
6	Memory Window and Endurance Improvement of Hf _{0.5} Zr _{0.5} O ₂ -Based FeFETs with ZrO ₂ Seed Layers Characterized by Fast Voltage Pulse Measurements. Nanoscale Research Letters, 2019, 14, 254.	5.7	63
7	Self-Confined Growth of Ultrathin 2D Nonlayered Wide-Bandgap Semiconductor CuBr Flakes. Advanced Materials, 2019, 31, e1903580.	21.0	61
8	Compatibility of HfN Metal Gate Electrodes With Hf _{0.5} Zr _{0.5} O ₂ Ferroelectric Thin Films for Ferroelectric Field-Effect Transistors. IEEE Electron Device Letters, 2018, 39, 1508-1511.	3.9	52
9	Hysteresis Reduction in Negative Capacitance Ge PFETs Enabled by Modulating Ferroelectric Properties in HfZrO _x . IEEE Journal of the Electron Devices Society, 2018, 6, 41-48.	2.1	51
10	Program/Erase Cycling Degradation Mechanism of HfO ₂ -Based FeFET Memory Devices. IEEE Electron Device Letters, 2019, 40, 710-713.	3.9	44
11	2-Bit/Cell Operation of Hf _{0.5} Zr _{0.5} O ₂ -Based FeFET Memory Devices for NAND Applications. IEEE Journal of the Electron Devices Society, 2019, 7, 551-556.	2.1	40
12	Electric Field Gradient-Controlled Domain Switching for Size Effect-Resistant Multilevel Operations in HfO ₂ -Based Ferroelectric Field-Effect Transistor. Advanced Functional Materials, 2021, 31, 2011077.	14.9	40
13	Grain Size Engineering of Ferroelectric Zr-doped HfO ₂ for the Highly Scaled Devices Applications. IEEE Electron Device Letters, 2019, 40, 1868-1871.	3.9	39
14	Thermally Stable and Radiation Hard Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ Thin Films on Muscovite Mica for Flexible Nonvolatile Memory Applications. ACS Applied Electronic Materials, 2019, 1, 919-927.	4.3	37
15	Subunit cell-level measurement of polarization in an individual polar vortex. Science Advances, 2019, 5, eaav4355.	10.3	31
16	Record-Low Subthreshold-Swing Negative-Capacitance 2D Field-Effect Transistors. Advanced Materials, 2020, 32, e2005353.	21.0	31
17	Ferroelectric Gate AlGaIn/GaN E-Mode HEMTs With High Transport and Sub-Threshold Performance. IEEE Electron Device Letters, 2018, 39, 79-82.	3.9	30
18	An ultrathin flexible electronic device based on the tunneling effect: a flexible ferroelectric tunnel junction. Journal of Materials Chemistry C, 2018, 6, 5193-5198.	5.5	29

#	ARTICLE	IF	CITATIONS
19	Structural and ferroelectric properties of Pr doped HfO ₂ thin films fabricated by chemical solution method. Journal of Materials Science: Materials in Electronics, 2019, 30, 5771-5779.	2.2	27
20	Characterization of domain distributions by second harmonic generation in ferroelectrics. Npj Computational Materials, 2018, 4, .	8.7	25
21	Improvement of remanent polarization of CeO ₂ -HfO ₂ solid solution thin films on Si substrates by chemical solution deposition. Applied Physics Letters, 2020, 117, .	3.3	21
22	Effects of Pb Doping on Hole Transport Properties and Thin-Film Transistor Characteristics of SnO Thin Films. ECS Journal of Solid State Science and Technology, 2015, 4, Q26-Q30.	1.8	19
23	Hf _{0.5} Zr _{0.5} O ₂ -Based Ferroelectric Field-Effect Transistors With HfO ₂ Seed Layers for Radiation-Hard Nonvolatile Memory Applications. IEEE Transactions on Electron Devices, 2021, 68, 4368-4372.	3.0	18
24	Difficulty of carrier generation in orthorhombic PbO. Journal of Applied Physics, 2016, 119, .	2.5	14
25	Interface Effects Induced by a ZrO ₂ Seed Layer on the Phase Stability and Orientation of HfO ₂ Ferroelectric Thin Films: A First-Principles Study. Physical Review Applied, 2021, 16, .	3.8	10
26	Mechanical Manipulation of Nano- ϵ -twinned Ferroelectric Domain Structures for Multilevel Data Storage. Advanced Functional Materials, 2021, 31, 2011029.	14.9	9
27	Total ionizing dose effects of ⁶⁰ Co γ -rays radiation on Hf _x Zr _{1-x} O ₂ ferroelectric thin film capacitors. Journal of Materials Science: Materials in Electronics, 2020, 31, 2049-2056.	2.2	8
28	Robustly stable intermediate memory states in HfO ₂ -based ferroelectric field-effect transistors. Journal of Materiomics, 2022, 8, 685-692.	5.7	5
29	Integration and Electrical Properties of Ferroelectric Hf _{0.5} Zr _{0.5} O ₂ Thin Film on Bulk β -Ga ₂ O ₃ (-201) Substrate for Memory Applications. IEEE Electron Device Letters, 2018, , 1-1.	3.9	4
30	Amorphous pnictide semiconductor BaZn ₂ As ₂ exhibiting high hole mobility. Applied Physics Letters, 2016, 109, .	3.3	2
31	The Effect of Kr/O ₂ /Sputtering on the Ferroelectric Properties of SrBi ₂ Ta ₂ O ₉ Thin Film Formation. IEICE Transactions on Electronics, 2019, E102.C, 441-446.	0.6	2
32	Flux-Closure Domains in PbTiO ₃ /SrTiO ₃ Multilayers Mediated without Tensile Strain. Journal of Physical Chemistry C, 2022, 126, 4630-4637.	3.1	1
33	A Highly Stable-Output Kilohertz Femtosecond Hard X-ray Pulse Source for Ultrafast X-ray Diffraction. Applied Sciences (Switzerland), 2022, 12, 4723.	2.5	1